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Correction: Epitaxial growth of GaN films on unconventional oxide substrates

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Correction for 'Epitaxial growth of GaN films on unconventional oxide substrates' by Wenliang Wang *et al.*, *J. Mater. Chem. C*, 2014, 2, 9342–9358.

Some of the parameters listed in Table 1 on the third page of this Feature Article were incorrect. The correct version of this table is given below with the revised values given in bold for clarity.

Table 1 Lattice parameters of unconventional oxide substrates and their epitaxial directions

Substrates	Lattice parameters			Epitaxial direction	Lattice mismatch %	Thermal mismatch %	Ref.
	<i>a</i> /nm	<i>b</i> /nm	<i>c</i> /nm				
GaN	0.3189	0.3189	0.5185	[0001]	0.0	0	11
Sapphire	0.4760	0.4760	1.2991	[0001]	13.3	27	11 and 12
LSAT	0.7730	0.7730	0.7730	[111]	1.0	3.6	13–15
LiAlO ₂	0.5169	0.5169	0.6260	[100]	0.3	21.3	16 and 17
LiGaO ₂	0.5402	0.6370	0.5007	[001]	0.2	16.6	18–20
LaAlO ₃	0.3791	0.3791	0.3791	[001]	3	39.2	21
MgAl ₂ O ₄	0.8083	0.8083	0.8083	[111]	9.0	37.9	22 and 23
MgO	0.4210	0.4210	0.4210	[111]	7	56.3	24 and 25
ZnO	0.3250	0.3250	0.5200	[0001]	0.4	7.6	26–28

Full details of the references cited in Table 1 can be found in the original article (DOI: 10.1039/c4tc01655f).

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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